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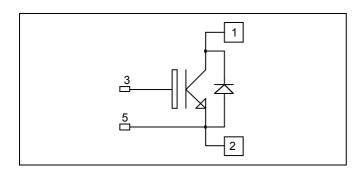




Single switch Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 1200V$$

 $I_{C} = 475A$ @ $Tc = 80$ °C



Application

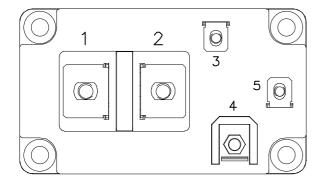
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	610	
	Continuous Conector Current	$T_C = 80$ °C	475	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	2082	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	800A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$; $V_{CE} = 1200V$				4	mA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 400A$	$T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$		1.8	2.2	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 10 \text{ mA}$		5	5.8	6.5	V

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			24.6		
Coes	Output Capacitance	$V_{CE} = 25V$			1.62		nF
C _{res}	Reverse Transfer Capacitance	f = 1MHz			1.38		
Q_{G}	Gate charge	V_{GE} = -8V / 15V I_{C} =400A	; V _{CE} =600V		2.3		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{CE} = 400A$			160		ns
$T_{\rm r}$	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				340		
T_{f}	Fall Time	$ \begin{array}{c} I_C = 400A \\ R_G = 1.8\Omega \end{array} $			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (150°C)		170		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 400A$			40		ns
$T_{d(off)}$	Turn-off Delay Time				450		
$T_{\rm f}$	Fall Time	$R_G = 1.8\Omega$			170		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150^{\circ}C$		44		mJ
E _{off}	Turn-off Switching Energy	$I_C = 400A$ $R_G = 1.8\Omega$	$T_{J} = 150^{\circ}C$		44		mJ
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; V_{Bus} $t_p \le 10 \mu s$; $T_j = 1$			1600		A

Diode ratings and characteristics

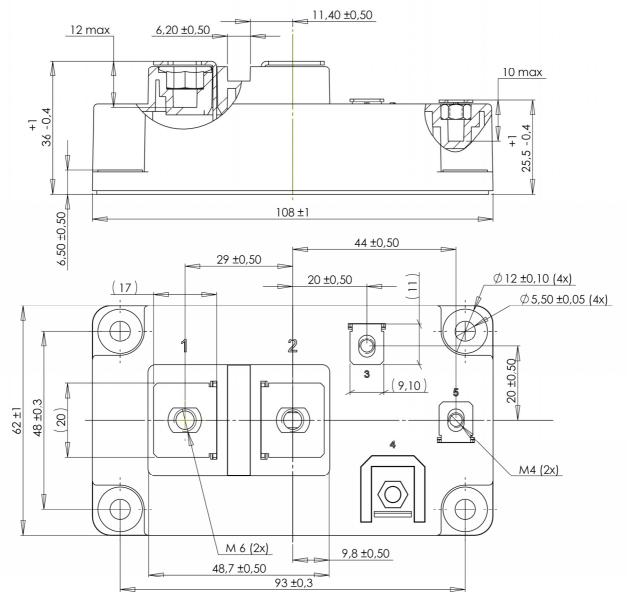
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	^
1RRM			$T_{j} = 150^{\circ}C$			2000	μA
I_F	DC Forward Current		$T_C = 80$ °C		400		A
V	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_j = 25^{\circ}C$		1.7	2.2	V
V_{F}			$T_{\rm j} = 150^{\circ}{\rm C}$		1.65		v
$t_{\rm rr}$	Reverse Recovery Time		$T_j = 25$ °C		155		ns
ι _{rr}	Reverse Recovery Time	I - 400 A	$T_{j} = 150^{\circ}C$		300		115
0	Q_{rr} Reverse Recovery Charge $I_F = 400A$ $V_R = 600V$ $di/dt = 7000A$		$T_j = 25^{\circ}C$		37.2		C
Qrr		$di/dt = 7000A/\mu s$	$T_j = 150$ °C		78		μС
E_{rr}	Reverse Recovery Energy		$T_j = 25$ °C		16		mJ
Ľm	Reverse Recovery Ellergy		$T_{j} = 150^{\circ}C$		32		1113



Thermal and package characteristics

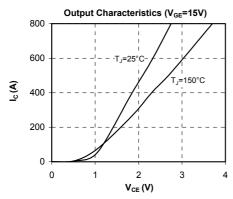
Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.072	°C/W	
1\(\text{thJC}\)		Diode			0.14	C/ W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}, 50/60 \text{Hz}$		4000			V	
T_{J}	Operating junction temperature range		-40		175		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature		-40		125		
Torque	Mounting torque	M6	3		5	N.m	
		M4	1		2	111.111	
Wt	Package Weight				350	g	

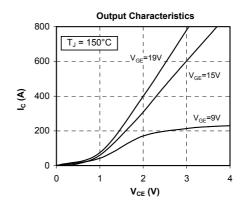
D4 Package outline (dimensions in mm)

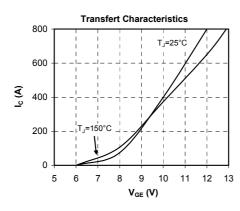


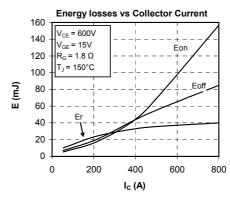


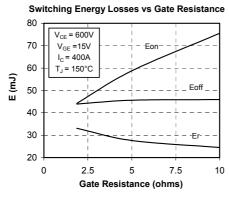
Typical Performance Curve

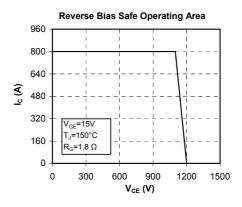


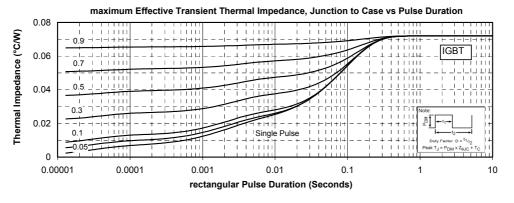




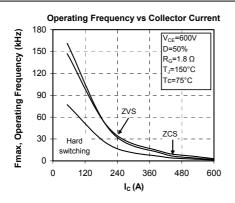


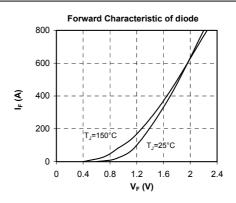


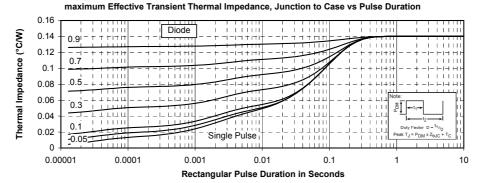














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